

Amendments to the Claims:

1 – 10 (Withdrawn)

11. (Currently amended) An I/C chip suitable for wire bonding comprising:
at least one conductive bond pad;
at least one layer of dielectric material overlying said conductive bond pad;
a surface defining an opening in said layer of dielectric material exposing said conductive
bond pad; ~~and~~
a conductive seed layer disposed in said opening at least one layer of conductive material
overlying said conductive bond pad and in contact therewith and in contact with the entire
surface of said opening and having at least one exposed edge; and also overlying and in contact
~~with the entire surface of said opening~~
at least one layer of said conductive material overlying said conductive seed layer and
completely covering said conductive seed layer including all exposed edges.

12. (Currently amended) The ~~invention~~ I/C chip as defined in claim 11
wherein there are two layers of conductive material plated on said conductive seed layer ~~bond~~
~~pad~~ in said opening.

13. (Currently amended) The ~~invention~~ I/C chip as defined in claim 12
wherein said two layers of conductive material are Ni and Au.

14. (Canceled)

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15. (Currently amended) The ~~invention~~ I/C chip as defined in claim 14 wherein an intermediate conductive layer is provided between said conductive seed layer and said conductive bond pad.

16. (Currently amended) The ~~invention~~ I/C chip as defined in claim 15 wherein the intermediate conductive layer is TaN/Ta.

17. (Currently amended) The ~~invention~~ I/C chip as defined in claim 11 wherein the conductive bond pad in the I/C chip is Al.

18. (New) The I/C chip as defined in claim 11 wherein said at least one layer of conductive material defines a wall in said I/C chip in which is disposed a ball bond and wire.

19. (New) The I/C chip as defined in claim 18 wherein the ball bond is Au.